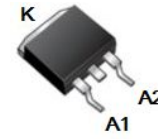
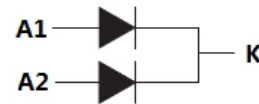
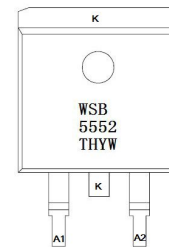


**WSB5552TH**
**Power Schottky Barrier Rectifier**
[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)
**Features**

- 2x5A average rectified forward current
- Low forward voltage and Low leakage current
- Excellent high junction temperature stability
- High forward surge capability


**TO-263E-2L**

**Circuit**

**Marking**
**Applications**

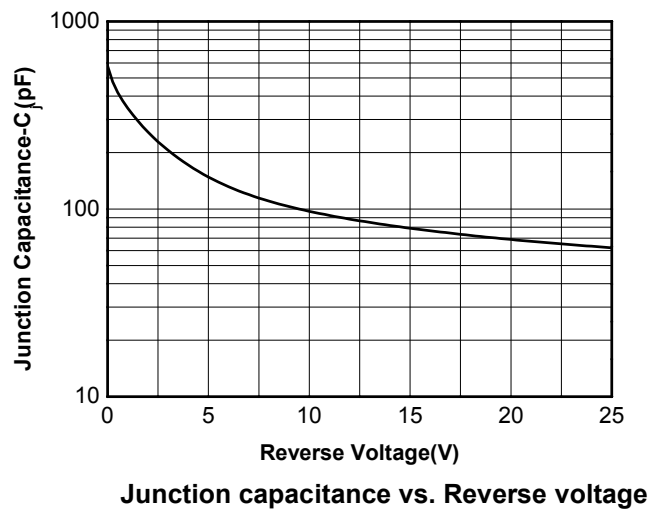
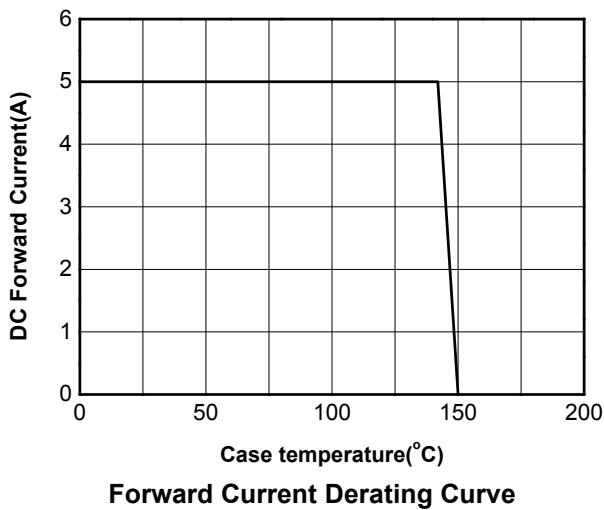
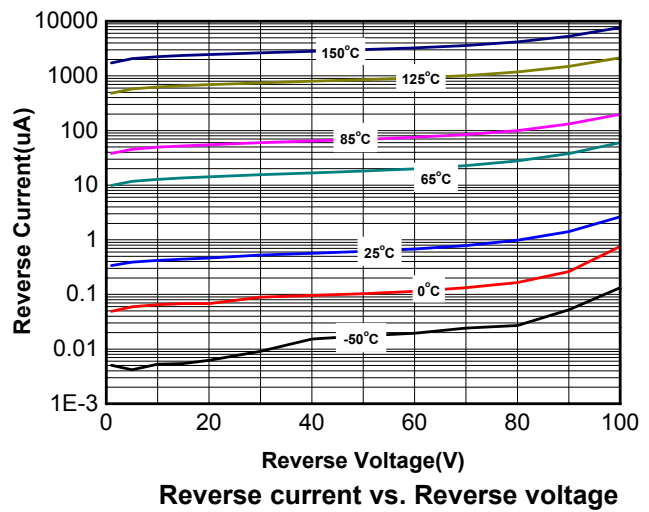
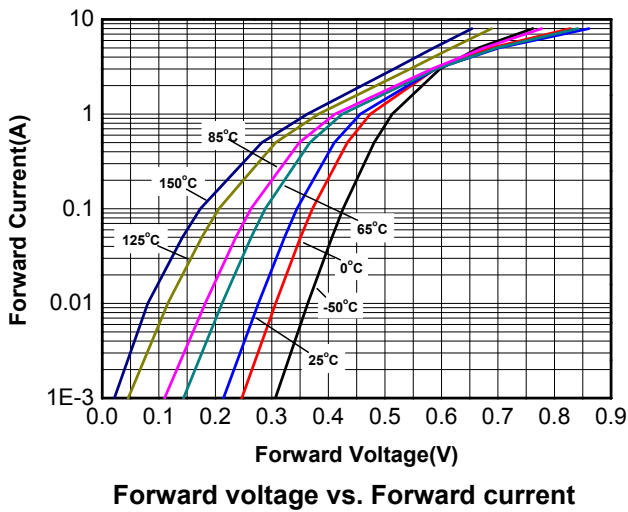
- High frequency switch model power supplies
- DC-DC Convertors, Power adapters

Absolute maximum ratings				
Parameter		Symbol	Value	Unit
Reverse voltage (repetitive peak)		$V_{RM}$	100	V
Reverse voltage (DC)		$V_R$	100	V
Average rectified forward current	Per diode	$I_F$	5	A
	Per device	$I_F$	10	A
Peak Forward Surge Current <sup>(1)</sup>		$I_{FSM}$	100	A
Junction temperature		$T_J$	150	°C
Operating temperature		$T_{opr}$	-55 ~ 150	°C
Storage temperature		$T_{stg}$	-55 ~ 150	°C
Thermal Resistance Ratings				
Maximum Thermal Resistance Junction To case (Per leg)		$R_{\theta JC}$	2.2	°C/W

Order information			
Device	Package	Marking	Shipping
WSB5552TH-3/T	TO-263E-2L	WSB5552THYW <sup>(2)</sup>	800/Reel&Tape

**Note 1: Pulse Width=8.3ms, Single Half Sine Pulse**
**Note 2: WSB5552= Device code;TH=Special Code; Y=Year; W=Week (A~z)**

Electronics characteristics (T <sub>A</sub> =25°C, Per diode)						
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V <sub>R</sub>	I <sub>R</sub> =0.5mA	100	-	-	V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =5A	-	-	0.80	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =100V	-	-	0.1	mA
Junction capacitance	C <sub>J</sub>	V <sub>R</sub> =25V, F=1MHz	-	62	-	pF

**Typical characteristics (T<sub>a</sub>=25°C, Per diode)**


**TO-263E-2L**
